

RT1P434X SERIES

〈Transistor〉

Transistor With Resistor
For Switching Application
Silicon PNP Epitaxial Type

DESCRIPTION

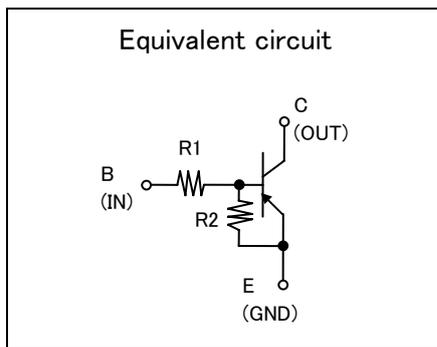
RT1P434X is a one chip transistor with built-in bias resistor, NPN type is RT1N434X.

FEATURE

• Built-in bias resistor (R1=4.7kΩ, R2=22kΩ).

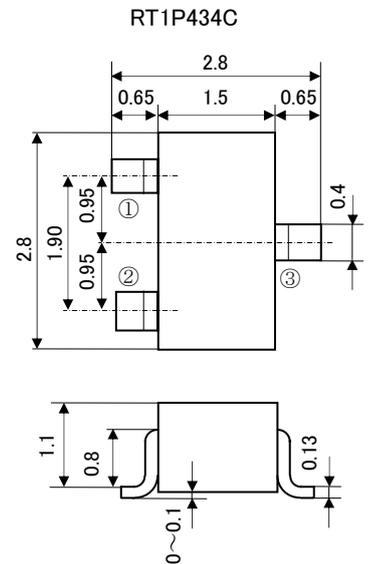
APPLICATION

. Inverted circuit, switching circuit, interface circuit, driver circuit.



OUTLINE DRAWING

UNIT : mm



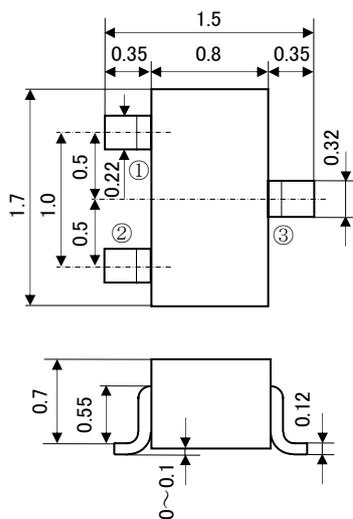
JEITA: SC-59

JEDEC: Similar to TO-236

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

RT1P434U



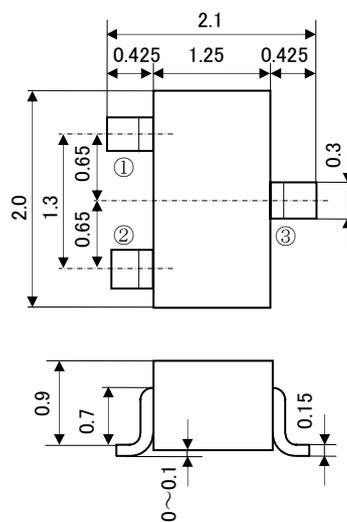
JEITA: SC-75A

JEDEC: —

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

RT1P434M



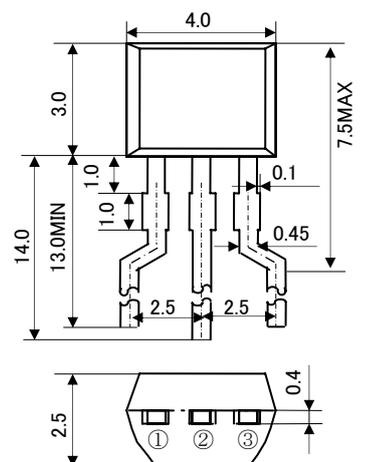
JEITA: SC-70

JEDEC: —

Terminal Connector

- ①: Base
- ②: Emitter
- ③: Collector

RT1P434S



JEITA: —

JEDEC: —

Terminal Connector

- ①: Emitter
- ②: Collector
- ③: Base

RT1P434X SERIES

〈Transistor〉

Transistor With Resistor

For Switching Application

Silicon PNP Epitaxial Type

MARKING

RT1P434C RT1P434M RT1P434U	RT1P434S

MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING				UNIT
		RT1P434U	RT1P434M	RT1P434C	RT1P434S	
V _{CBO}	Collector to Base voltage	-50				V
V _{EBO}	Emitter to Base voltage	-6				V
V _{CEO}	Collector to Emitter voltage	-50				V
V _{IN}	Input voltage	-30				V
I _C	Collector current	-100				mA
I _{CM}	Peak Collector current	-200				mA
P _C	Collector dissipation(Ta=25°C)	150	200	450	mW	
T _j	Junction temperature	+150				°C
T _{stg}	Storage temperature	-55~+150				°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
V _{(BR)CEO}	C to E breakdown voltage	I _C = -100 μA, R _{BE} = ∞	-50	—	—	V
I _{CBO}	Collector cut off current	V _{CB} = -50V, I _E = 0	—	—	-0.1	μA
I _{EBO}	Emitter cut off current	V _{EB} = -5V, I _C = 0	-147	-187	-259	μA
h _{FE}	DC forward current gain	V _{CE} = -5V, I _C = -5mA	50	—	—	—
V _{CE(sat)}	C to E saturation voltage	I _C = -10mA, I _B = -0.5mA	—	—	-0.3	V
V _{I(ON)}	Input on voltage	V _{CE} = -0.2V, I _C = -5mA	—	-0.9	-1.7	V
V _{I(OFF)}	Input off voltage	V _{CE} = -5V, I _C = -100 μA	-0.5	-0.7	—	V
R ₁	Input resistor	—	3.3	4.7	6.1	kΩ
R ₂ /R ₁	Resistor ratio	—	4.2	4.7	5.1	—
f _T	Gain band width product	V _{CE} = -6V, I _E = 10mA	—	150	—	MHz

RT1P434X SERIES

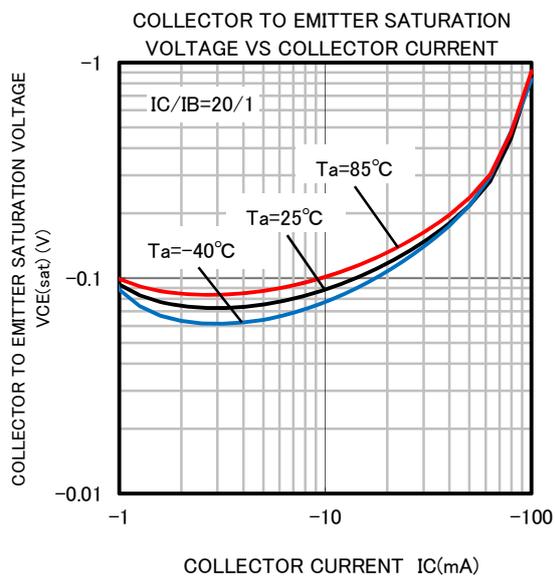
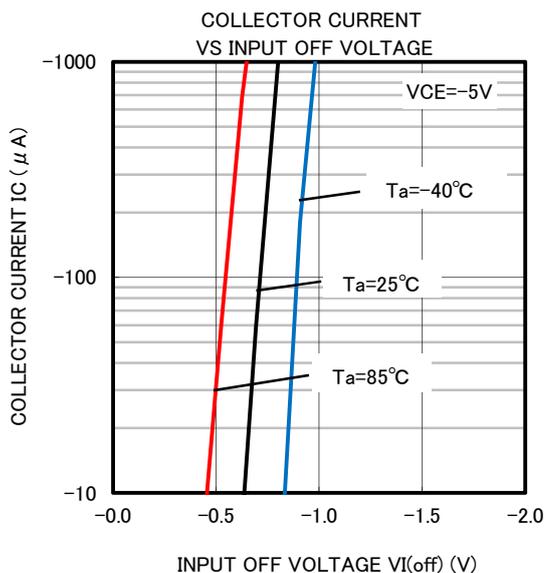
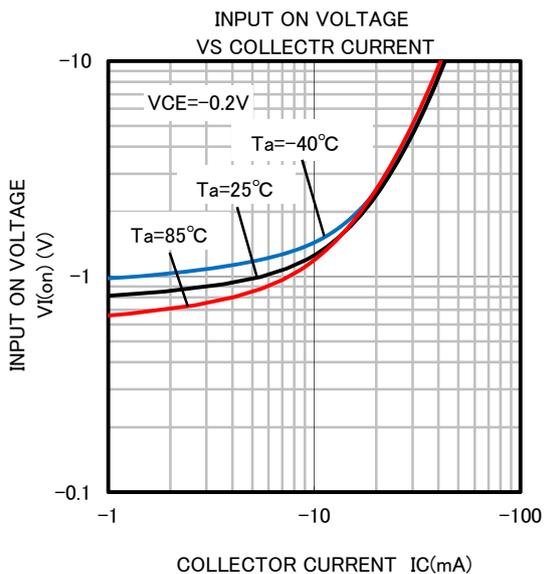
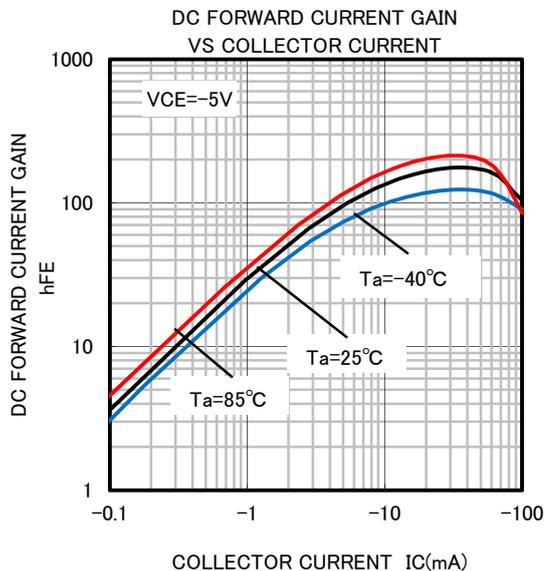
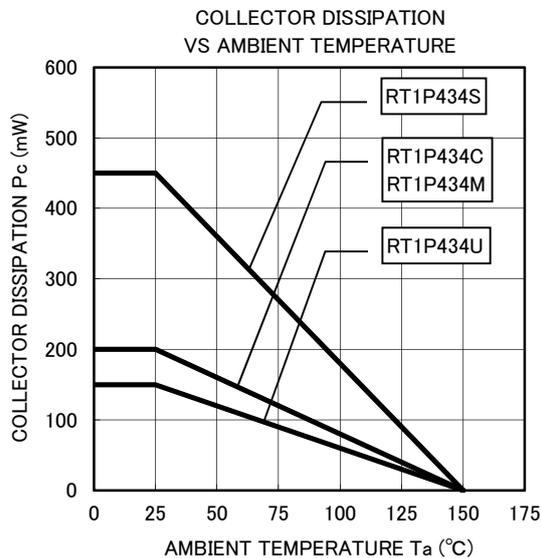
〈Transistor〉

Transistor With Resistor

For Switching Application

Silicon PNP Epitaxial Type

TYPICAL CHARACTERISTICS





Keep safety first in your circuit designs!

·ISAHAYA Electronics Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (1) placement of substitutive, auxiliary, (2) use of non-flammable material or (3) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to our customers in the selection of the ISAHAYA products best suited to the customer's application; they don't convey any license under any intellectual property rights, or any other rights, belonging ISAHAYA or third party.
- ISAHAYA Electronics Corporation assumes no responsibility for any damage, or infringement of any third party's rights, originating in the use of any product data, diagrams, charts or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams and charts, represent information on products at the time of publication of these materials, and are subject to change by ISAHAYA Electronics Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact ISAHAYA Electronics Corporation or an authorized ISAHAYA products distributor for the latest product information before purchasing product listed herein.
- ISAHAYA Electronics Corporation products are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact ISAHAYA Electronics Corporation or an authorized ISAHAYA products distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- The prior written approval of ISAHAYA Electronics Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination. Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- Please contact ISAHAYA Electronics Corporation or authorized ISAHAYA products distributor for further details on these materials or the products contained therein.